



2818

PATENT APPLICATION
Do. No. 4591-224

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Ki-Nam KIM and Yoon-Jong SONG

Serial No. 10/066,172

Examiner: Tran, Long K

Confirmation No. 2722

Filed: January 30, 2002

Group Art Unit: 2818

For: FERROELECTRIC MEMORY DEVICE AND METHOD OF FORMING
THE SAME

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BOX NON FEE AMENDMENT
Assistant Commissioner for Patents,
Washington, D.C. 20231

Responsive to the Office Action dated October 16, 2002, enclosed is an amendment in the above-identified application.

The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For:	Number After Amendment	Previous Number	Extra	Rate	Additional Fee
Total Claims	4	24	0	x \$18 =	\$0
Independent Claims	1	4	0	x \$84 =	\$0
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0

*greater of twenty (20) or number for which fee has been paid

**greater of three (3) or number for which fee has been paid

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



20575

PATENT TRADEMARK OFFICE

Alan T. McCollom
Reg. No. 28,881

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THEY CERTIFY THAT
THE INVENTOR IS BEING OF
THE UNITED STATES
OF THE FIRST CLASS
AND ADDRESS TO
THE INVENTOR OR ATTORNEY
IN THE UNITED STATES

BY: [Signature]
DATE: 1/23/03
FEE: \$0
CLASS: 3600
MARKS: 0900
STATION: VA 22202-9901



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RESPONSE TO OFFICE ACTION

Responsive to the Office Action dated October 16, 2002, please amend the application as follows.

IN THE CLAIMS

For the Examiner's convenience, any and all amendments to the pending claims are incorporated and presented below in clean form.

21. (Amended) A ferroelectric memory device comprising:
a first interlayer insulating layer formed on a semiconductor substrate;
a buried contact structure electrically connected to the substrate through a first contact hole extending through the first interlayer insulating layer, the buried contact structure formed on the first interlayer insulating layer;
a blocking layer formed on the buried contact structure and the first interlayer insulating layer;
a second interlayer insulating layer formed on the blocking layer; and
a ferroelectric capacitor that fills a second contact hole and connects to the buried contact structure through the second contact hole that penetrates the second interlayer insulating layer and the blocking layer, the ferroelectric capacitor being formed on the second interlayer insulating layer.